

ORGANO-ELECTRONIC DEVICE AND ITS FABRICATING METHOD

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Abstract of JP2003258164

<P>PROBLEM TO BE SOLVED: To provide an organo-electronic device in which variation or deterioration of characteristics due to atmosphere is improved, and a method for fabricating an organo-electronic device conveniently at a low cost. **<P>SOLUTION:** The organo-electronic device has an organo-electronic material layer 13 where at least a part of the organo-electronic material layer 13 is sealed with an alumina sealing film 14. In the method for fabricating an organo-electronic device, the sealing film 14 is formed by depositing an alumina film at a part being sealed with the sealing film 14 using an RF sputtering system. **<P>COPYRIGHT:** (C) 2003,JPO

